## Precision Timing in HEP Experiments

An 8－fold way．．．


黄色い！


Orange
Grün！

Gary S．Varner

( $x, y, z ; t$ ) - As a neverending student
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- Learn 'Time’ is a fiction
( $x, y, z ; t$ ) - As a neverending student
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- Heisenberg Uncertainty
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$$
\Delta E \Delta t \geq \npreceq / 2
$$

（ $x, y, z ; t$ ）－As a neverending student
－Learn＇Time＇is a fiction
－Heisenberg Uncertainty

$$
\begin{array}{r}
\Delta E \Delta t \geq K / 2 \\
\text { 小林 益川 }
\end{array}
$$

$$
V_{\mathrm{CKM}} \equiv V_{L}^{u} V_{L}^{d \dagger}=\left(\begin{array}{ccc}
V_{u d} & V_{u s} & V_{u b} \\
V_{c d} & V_{c s} & V_{c b} \\
V_{t d} & V_{t s} & V_{t b}
\end{array}\right)
$$

Measurement of $\sin \left(2 \varphi_{1}\right) / \sin (2 \beta)$ in $\mathrm{B} \rightarrow$ Charmonium $\mathrm{K}^{0}$ modes


Overpowering evidence for CP violation (matter-antimatter asymmetries). >>>> The phase of $\mathrm{V}_{\text {td }}$ is in good agreement with Standard Model expectations. This is the phase of $B_{d}$ mixing.

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- 10 's of ps
- ~1ps
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Trailokya (Sanskrit: त्रैलोक्य; Pali: tiloka, Wylie: khams gsum) has been translated as "three worlds,"[1][2][3][4][5] "three spheres,"[3] "three planes of existence,"[6] "three realms"[6] and "three regions."[4] These three worlds are identified in Hinduism and appear in early Buddhist texts.

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> My difficulty
> (1) Null set (3) Focus
> (3) Mix of 2
> (1) Overview of each

## The canonical example: HL-LHC

- Luminosity of $5 \times 10^{34} \mathrm{~cm}^{-2} \mathrm{~s}^{-1}$ corresponds to an *average* pileup of 140 events
- Upper estimate of average number of pileup events for this lumi partly accounts for bunch-to-bunch variation
- Average of a Poisson distribution with a sigma of about 12 events
- Key questions:
- Can the detectors work with even higher (average) pileup to allow 3000 /fb to be delivered more quickly?
- Can a longer beam spot help pileup mitigation?
- Need to take into account in-time pileup (same bunch crossing) and out-of-time pileup (previous crossings) - particularly for ATLAS colorimeter and for muon spectrometers



## Low-Gain Avalanche Detectors (LGAD)



Principle:
Add to n-on-p Silicon sensor an extra thin p-layer below th junction which increases the E-field so that charge multiplication with moderate gain of 1050 occurs without breakdown.

High Doping Concentration: High Field


Manufacturers of LGAD ( $30 \mu \mathrm{~m}-300 \mu \mathrm{~m}$ ): CNM Barcelona (RD50, ATLAS-HGTD) HPK Hamamatsu FBK Trento (INFN)
very similar behavior with exception of breakdown voltage and special design features.


Figure 1 Screenshot of one event, showing the signals of 3 LGAD biased at 200 V and the SiPM at 28 V . Each horizontal division corresponds to 2 ns , while each

3 identical $45 \mu \mathrm{~m}$ thick $1.3 \times 1.3 \mathrm{~mm}^{2}$ LGAD produced by CNM

To extract the time stamp of the LGAD employ constant-fraction discrimination (CFD) to correct for time walk (CFD $\approx 20 \%$ ).

Important: this can be reliably implemented in an ASIC.

Timing resolution vs. \# of UFSD averaged


- Good matching of three LGAD
- Time resolution of single UFSD:
~ 25 ps (240V)
- Time resolution of average of 3 UFSD: 20 ps (200V) \& 16 ps (240V)
- Timing resolution agrees with expectation $\sigma(N)=\sigma(1) / N^{0.5}$


## LAPPDs -> MCP timing



- Each 'pixel' is 20 "
- Fragile, expensive
- Few ns timing
- Neutrino cross-section can't be fooled
- $40 \%$ photocathode coverage
$><100$ ps timing
$><\mathrm{cm}$ pos. resolution
$>$ Significantly larger number of voxels
$>$ Larger fiducial volume


## Production single photon testing

Laser timing: laser_pixel3_0_gain4_HV3201_18may2015


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- Switches, comparators
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- References and temp compensation


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- TAC + TDC (simple counter)


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- Student projects

1. Actually build test circuits
2. High quality analog difficult
3. Sub-10ps not so difficult

## So What is the Disconnect?

## Summary of TOF System Timing Resolution


L. Ruckman, G. Varner, NIM A602 (2009) 438-445

## Fast, Focusing-DIRC Experience



## "25ps CFD in lab"

-End Station A environment

## Picosecond needs

## Askaryan Calorimeter Exp (ACE)



## Radio (mm wave)

## arXiv:1708:01798 (5-AUG-2017) 2.3ps intrinsic timing resolution (SLAC ESTB measurement)

ACE channel-to-channel cross-correlation relative timing delays


## Predictions from the last decade

1 GHz analog bandwidth, 5GSa/s

Time Difference Dependence on Signal-Noise Ratio (SNR)

G. Varner and L. Ruckman NIM A602 (2009) 438-445.

Simulation includes detector response


J-F Genat, G. Varner, F. Tang, H. Frisch NIM A607 (2009) 387-393.

## Interest in exquisite space-time Resolution

In a number of communities (future particle/astroparticle detectors, PET medical imaging, etc.) a growing interest in detectors capable of operating at the pico-second resolution and $\mu \mathrm{m}$ spatial resolution limit (for light 1 ps $=300 \mu \mathrm{~m}$ )


Front-End Electronics


Fast signal collection x-ray detectors

## Toward increased timing precision

| ASIC | \# chan | Depth/chan | Time Resolution [ps] | Vendor | Size [nm] | Year |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| LABRADOR 3 | 8 | 260 | 16 | TSMC | 250 | 2005 |
| BLAB | 1 | 65536 | 1-4 | TSMC | 250 | 2009 |
| STURM2 | 8 | 4x8 | <10 (3GHz ABW) | TSMC | 250 | 2010 |
| DRS4 | 8 | 1024 | ~1 (short baseline) | IBM | 250 | 2014 |
| PSEC4 | 6 | 256 | ~1 (short baseline) | IBM | 130 | 2014 |
| RITC3 | 3 | Continuous | TBD | IBM | 130 ? | --- |
| PSEC5 | 4 | 32768 | TBD | TSMC | 130 | --- |
| DRS5 | 8/16? | $128 \times 32$ | TBD | UMC | 110 | --- |
| SamPic | 16 | 64 | $\sim$ few [pic 0] | AMS | 180 | [2014] |
| RFpix | 128? | TBD | <= 100fs (target) | TSMC | 130 ? | --- |

Very incomplete: missing S. Kleinfelder ASIC from yesterday

## Constraint 1: Analog Bandwidth

## Difficult to couple in Large BW (C is deadly)



## Constraint 2: kTC Noise

Want small storage C, but...


## Constraint 3: Leakage Current

## Increase C or reduce conversion time $\ll 1 \mathrm{mV}$



## Sample channel-channel variation

$\sim$ fA $\rightarrow$ nA leakage ( $250 \mathrm{~nm} \rightarrow$ 130nm)

## The ultimate Space-Time Limit

- How to measure something extremely precisely in HEP?

The ultimate Space-Time Limit

- How to measure something extremely precisely in HEP?

Cancel systematic errors in ratio

## What would it take?



- Micron spatial pixel resolution (using timing)
$\rightarrow$ Fast timing brings many benefits:
> Minimal pile-up (fast clearing)
$>$ Improved event timing (direct TO for TOF/TOP measurements)
> Belle II data archiving!


## Exploration of the space-time limit

-Sampling at high sampling rate and high bandwidth
-Resolve small distances
Current Goals: Spatial resolution of $10 \mu \mathrm{~m}$ in z and $20 \mu \mathrm{~m}$ in $\mathrm{r} \varphi$
In Silicon $10 \mu \mathrm{~m}$ in z corresponds to timing resolution of about 100fs $20 \mu \mathrm{~m}$ in $\mathrm{r} \varphi$ will depend on the SNR



Pixel detector (PDX) at SuperKEKB

## Signal Propagation




## Spatial resolution correlation



## Performance Parameter Space





## Overall optimization/interplay



## Target Specifications

| Parameter | Minimum desired value |
| :--- | :---: |
| Sampling frequency (ASIC) | 20 GHz |
| Bandwidth (Detector and ASIC) | 3 GHz |
| Signal to Noise Ratio (Detector and ASIC) | $58 \mathrm{~dB}\left(\mathrm{~V}_{\text {signal }}=1\right.$ Volt) |
| Velocity of Propagation (Transmission <br> Line/ strip line) | 0.35 c |
| Number of Bits of Resolution | 9.4 bit |

This is an ongoing study - snapshot PhD student needs to finish $\rightarrow$ focus on ASIC A device with <=1ps (independent of aperture) interesting PSEC4 design as a reference $\rightarrow$ PSEC5 design


## PSEC4

## PSEC5 $\rightarrow$ us

 sampling latency

## PSEC4: Sampling Analysis

Utilizing PSEC4's SCA as starting place
-Adjustable Sampling rate between 4-15 GSPS
-1.6 GHz bandwidth


## Equivalent Circuit

Multichannel<br>sampling array



Gain vs Frequency


- First Call ON wo Par
- First Cell ON w' Par
----- First 2 Cells ON w/Par
......... First 3 Cells ON w/ Par


# Simulation Results: Bandwidth for worst case operating bias point 

Whether the $1^{\text {st }}$ switch is on or the last, Gain is the same


## Pass Transistor (Switch) Resistance

TRACK state


- Ron=2.4k @665mVdc

HOLD state


- Roff is in $\mathbf{G} \Omega$
- The PFET and NFET are not matched and Ron varies considerably


## Small signal frequency response



- BWworst 2.3 GHz @665mVdc @LowZ drive
- BWworst $\approx 1.7 \mathrm{GHz}$ @665mVdc @ $50 \Omega$ drive

- Isolation is over 60 dB over all parameter space


## Summary

'Precision Timing' has different meanings

- 10's of picoseconds:
> HL-LHC, MCP-PMTs, TOF-PET
> Many WFS, TDC options: amplifier challenge
> System engineering
- ~1ps:
> Space-time Detector determined
> Direct conversion techniques
- Femtosecond:
$>$ Differential techniques
> Pushing the equivalent space-time limit


## Back-up slides



## PSEC4 Analysis: Single Sampling Cell

Input pad

Transmission line

> Sampling cell (1 unit)

## PSEC4 Analysis: Single Sampling Cell

Structure \& Layout


Side view
Transmission line

Thick Metal


## Single Sampling Cell Coupling

Simplified Schematic


- Driver circuit
- Switch with n-p FET pair
- Sampling capacitor
- Comparator as load

Switch \& Sampling Capacitor Equivalent Circuit


- Check Csampling capacitance
- Identify Ron and Roff


## Simulation Results: Group Delay

Group Delay does vary depending which switch is on by $\sim 25$ ps which puts a constraint on sampling time window

........ last Cell ON w Parasitic C

- 1st Cell On wo Parasitic C
- 1st Call ON w/Parasitic C


## Simulation Results: Phase

- At higher frequencies Phase vs freq behavior is also different and depends on which switch is on



## Simulation Results: Capacitance

Capacitance is 2.2 pF and does not dependent on which switch is on

Capacitance vs Frequency


- 1st Cell ON w/Parasitic C
- 1st Cell On wo Parasitic C
$\ldots$....... last Call ON W/Parasitic C


## Sampling Capacitor Spread



Monte Carlo with process variation and mismatches shows a discrepancy between Csampling Schematic (13.5 fF) and Measured mean (20.27 fF).

The Spread is about 1.9 fF which makes the Capacitor tolerance at about 9.3\%

| Num. of <br> Samp. | MEAN | STD | MIN | MAX |
| :---: | :---: | :---: | :---: | :---: |
| 1000 | 20.27 fF | 1.89 fF | 14.86 fF | 26.24 fF |

# Frequency Analysis 

Performance: S(Z)-parameter


The input impedance is high and it is capacitive.

## Input coupling analysis



$$
Z_{11}=\frac{1+s C_{\text {OUT }} R}{s^{2} C_{I N} C_{\text {OUT }} R+s\left(C_{I N}+C_{\text {OUT }}\right)}
$$

The transfer function parts:

- input parasitic capacitance of the transistor plus capacitance of the transmission line section.
- Series resistance of the transistor channel (Rds)
- Output capacitance which is formed of the parasitic capacitance of the transistor, sampling capacitor and load capacitance

Capacitance values


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## Small signal phase analysis

Group Delay without the load


Group Delay with the load

$\rightarrow$ Large group delay variation points to large distortion

## Large signal response (I)



- Full dynamic range at low frequency, compression appears when reaching the voltage threshold of the PN junctions at the drain/substrate barrier.

- Gain compression at lower and higher amplitudes


## Large signal analysis (II)

High frequency gain compression \& distortion


Three region of operation:

- Low distortion \& High compression
- Moderate distortion \& Moderate compression
- High distortion \& High compression



## Understanding signal response

Low distortion \& High compression


- Resistance of the channel does not vary much -> Low distortion
- At high resistance the bandwidth is limited -> lowering of the gain (compression)

TRACK state


## Understanding signal response

- Resistance of the channel is varying

Moderate distortion \& Moderate compression

-> The bandwidth at instantaneous values of the incident voltage waveform is different
$\uparrow \quad->$ In frequency domain this gives rise to higher harmonics, which interfere constructively hence increasing the overall signal amplitude but also increases distortion

TRACK state


## Harmonic decomposition



- Constructive interference of odd harmonics and destructive interference of even harmonics at the peaks
- Constructive interference of second and third harmonics at zero crossing

Frequency domain decomposition



## Noise and Distortion

Input referred noise


- Noise dominated by the ON resistance of the channel

Integrated referred noise


- Total noise is around $0.29 \mathrm{mV} \pm 0.01$ mV


## Noise, distortion and dynamic range

Signal to Noise Ratio at full scale input (1Vin)


- $\quad$ SNR is around $61.7 \mathrm{~dB} \pm 0.3 \mathrm{~dB}$


## Distortion analysis



- Most of the distortion comes from the Ron variation over the input voltage range


## Transient Response



## Input Vdc voltage



600 mV 900 mV

- Worst case window time is 0.8 ns or 1.25 GHz -> due to low bandwidth
- Best case is 0.25 ns or 4 GHz

Transient response at $\mathbf{3 0 0} \mathbf{~ m V d c}$


- $15 \%$ backlash at 30 mV forward transient
- Pedestal error due to charge injection and transistor mismatch dominate


## Summary - Requirements comparison

| Parameter | Measured (worst case) | Requirement |
| :--- | :--- | :--- |
| Bandwidth | $1.7 \mathrm{GHz} @ 665 \mathrm{Vdc} @ 50 \Omega$ | 3 GHz |
| SNR | 61.7 dB | 58 dB |
| ENOB | 9.8 bits (small region) | 9.4 bits |

Things to improve:

- Reduce Ron variance over the dynamic range to reduce distortion and increase the ENOB
- Timebase generator stability
- Bandwidth improvement:
- Reduce Cin or reshape the channel to increase the bandwidth (first pole)
- Reduce Ron overall value to increase the bandwidth (second pole)
- In summary:
- Increase bandwidth
- Need fast detector
- Use differential configuration to reduce pedestal error and increase noise coupling and crosstalk immunity


## Ongoing Plans

- "Pixel" vertex detector using precision timing?
- PSEC5 ASIC
- $256 \rightarrow$ 32k sample storage
- Work to optimize bandwidth, ENOB
- Persistence effects
- RFpix ASIC
- Push limits of ABW, timing
- Below 100-200fs, direct spatial measurement becomes interesting
- Many practical issues, but none fundamental (CF 1ps)
- DRS5, SAMPIC ASICs
- Will be interesting to see how well can perform


## Visualizing parameters for time resolution in z



## Design Choices

- Input coupling
- Differential versus single-ended input
- Needed analog bandwidth
- Gain needed?
- Sampling Options
- On-chip PLL/DLL
- External DLL
- Analog transfer vs. interrogate in situ
- ADC and readout options
- Sequential output select vs. random access
- On-chip vs. off-chip ADC
- Serial, parallel, massively parallel

Many variants have been explored...

## SINAD \& ENOB assessment

SINAD $=-10 \log _{10}\left[10^{-\frac{S N R}{10}}+10^{\left.-\frac{T H D}{10}\right]}\right.$
ENOB versus frequency


- ENOB DOMINATED BY DISTORTION


## Now pushing to the femtosecond regime

Pushing sampling speed and analog bandwidth


And pushing the space-time limit (new type of PID or DIRC devices?)
P. Orel and G. Varner

IEEE Trans. Nucl. Sci. 64 (2017) 1950-1962.


